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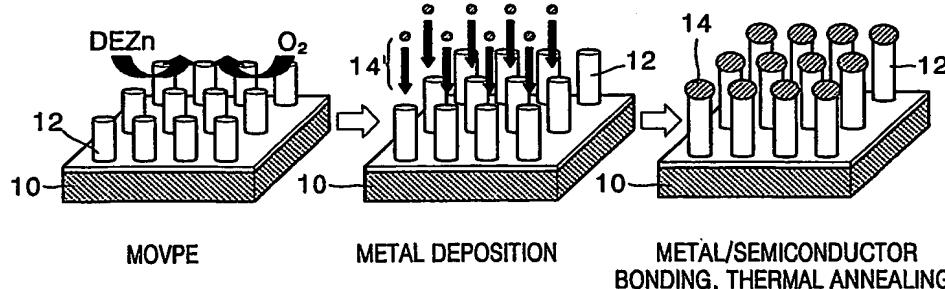
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(54) Title: CONTACTS FABRIC USING HETEROSTRUCTURE OF METAL/SEMICONDUCTOR NANORODS AND FABRICATION METHOD THEREOF



(57) Abstract: Provided are a contact fabric using a heterostructure of metal/semiconductor nanorods and a method of manufacturing the same. An ohmic contact fabric having a low contact resistance or a Schottky contact fabric having a rectification characteristic is formed by selectively depositing metal of nano-sizes onto predetermined portions of zinc oxide/semiconductor nanorods and controlling the work function of the deposited metal and the interfacial characteristics of metal/zinc oxide. The contact fabric can be applied to various nano-sized electronic devices, including Schottky diodes, optical devices, and arrays thereof.

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